



UNIVERSITÀ  
DI CAMERINO



Trento Institute for  
Fundamental Physics  
and Applications

# tHEEOM-RD

technology for High Efficiency Electro-Optical Modulator

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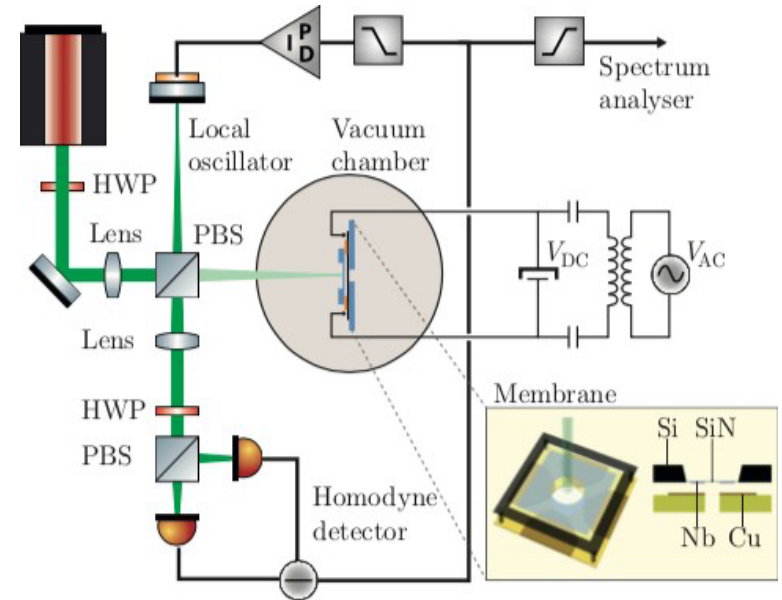
# Electro-Optical mechanical modulators exploiting the electro-opto-mechanical interaction for transduction of weak rf signals

## Quantum networks

**Light** is optimal for quantum communications between nodes, while **microwaves** are used for manipulating solid state quantum processors

Quantum interface between optical and microwave photons would be extremely useful: **optimal solid state qubits – optical photon transducer (Opto- electro-mechanical systems)**

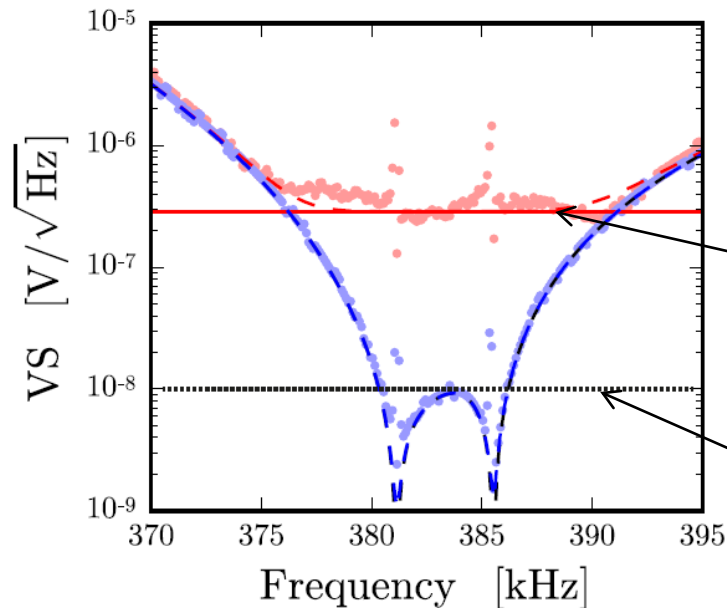
## High-sensitive optical detection of an rf signal:



## Applications (classical domain):

- **RF high efficiency sensors in NMR** - KAZUYUKI TAKEDA et al. Electro-mechano-optical detection of nuclear magnetic resonance - Optica 2018
- **RF EOM could integrate non-reciprocal devices (without the use of magneto-optic effect) RF-isolators/RF circulators** X. W. Xu et al., Nonreciprocal conversion between microwave and optical photons in electro- optomechanical systems, Phys. Rev. A 93, 023827 (2016).

## High-sensitive optical detection of a weak rf signal



Voltage sensitivity = 300  
 $\text{nV}/\sqrt{\text{Hz}}$  over a 15 kHz  
bandwidth with rf-noise added

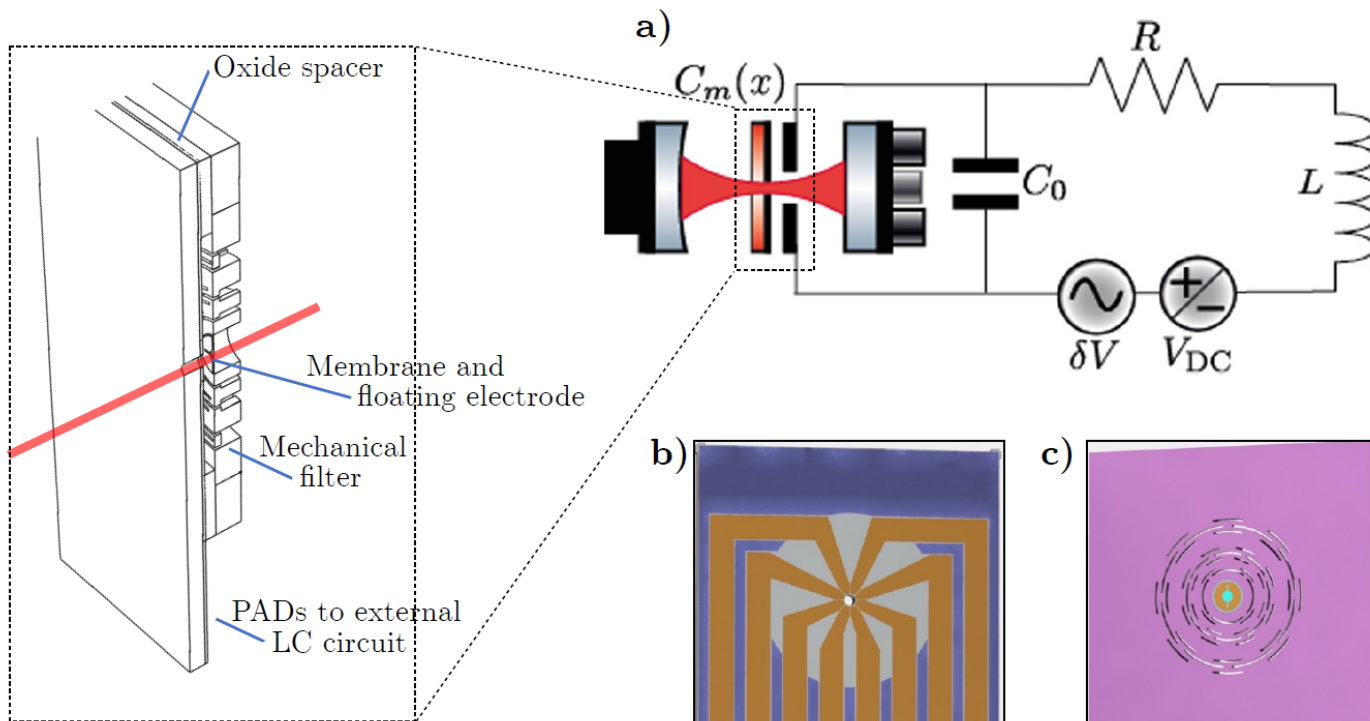
Optimal shot-noise limited  
sensitivity = 10  $\text{nV}/\sqrt{\text{Hz}}$  over a 5  
kHz bandwidth (negligible rf  
noise)

I. Moaddel Haghghi, N. Malossi, R. Natali, G. Di Giuseppe, and D. Vitali, Phys. Rev. Applied **9**, 034031 (2018)

**Theom\_RD** aims at improving the device: **better membrane capacitor**  $\Rightarrow$

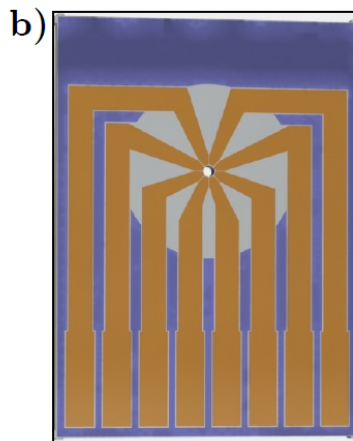
- improved transduction efficiency
- reduced added noise
- increased bandwidth
- possibility to operate in the quantum regime at ultracryogenic temperatures

# SCHEME OF THE OPTO-ELECTRO-MECHANICAL MODULATOR

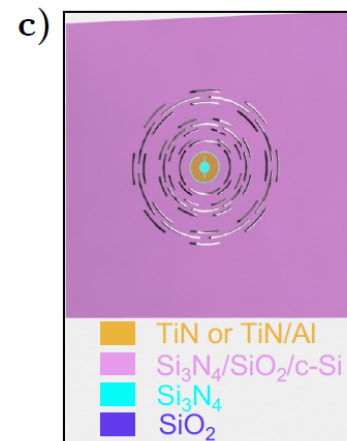


## Design requirements

- **High mechanical Q**  $\sim 10^6$  (low thermal noise)
- **Small gap d between** capacitor electrodes and large effective capacitor area  $A_{\text{eff}}$  for strong enough electromechanical coupling



Electrode connected to the LC circuit



Floating electrode on the SiN membrane

$$C(\hat{x}) = C_0 + C_m(\hat{x}) = C_0 + \frac{\epsilon_0 A_{\text{eff}}}{h_0 + \hat{x}}$$

# MAIN STEPS OF THE MICROFABRICATION PROCESS FLOW-CHART

TIPFA Trento, EKL TU Delft

1- Deposition of the rf-sputtered TiN/Al layers



3- Deposition of the Al protection layer



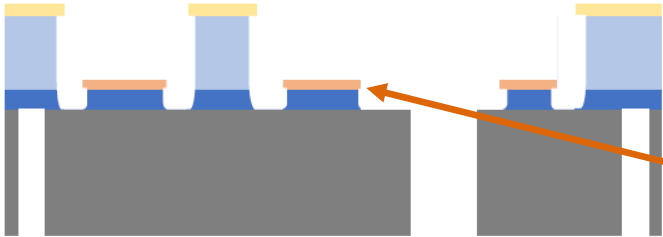
2- PECVD oxide (5 um) and protective mask (Al/PECVD oxide)



4- Deep-RIE etching

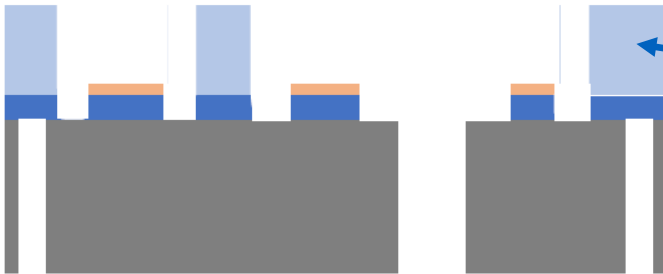


5- Wet etching by BOE 7:1



Floating electrode (TiN 50 nm)  
(membrane, Si<sub>3</sub>N<sub>4</sub> 100 nm)

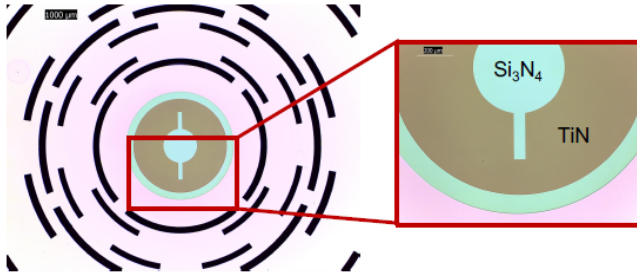
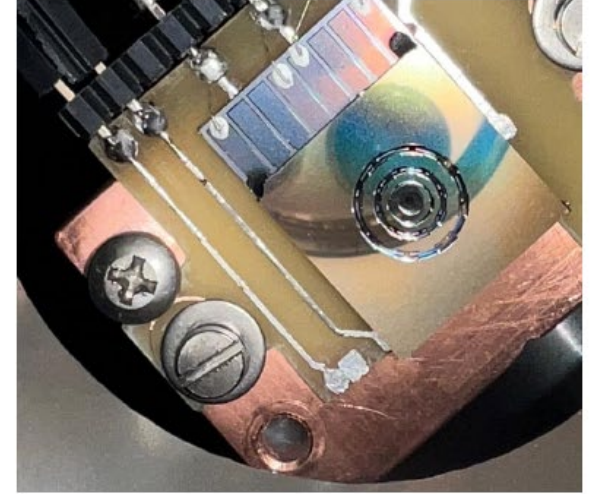
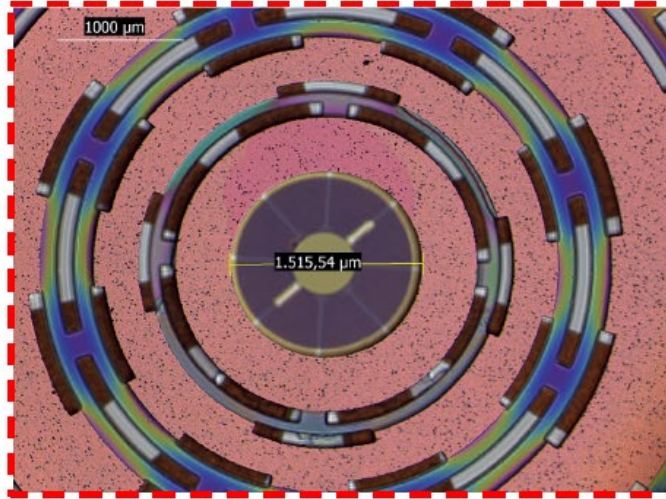
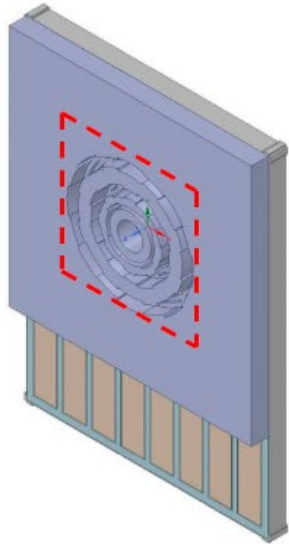
6- Dry etching oxide step and PES



Oxide spacer (3-10 um)

- PECVD SiO<sub>2</sub>
- Thermal SiO<sub>2</sub>
- TiN/Al
- Al
- Si

# ASSEMBLED DEVICE

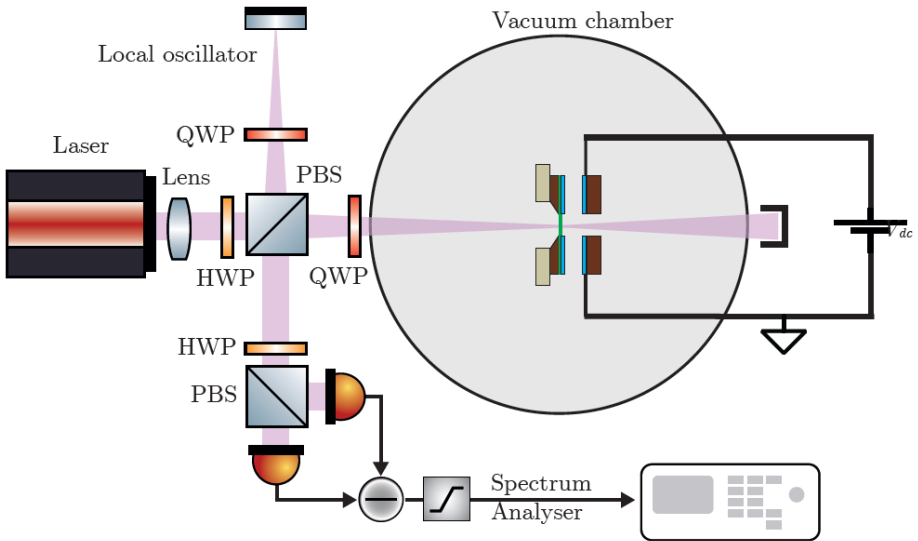


Left: Detailed view of the interaction region in the OEMM assembled device.

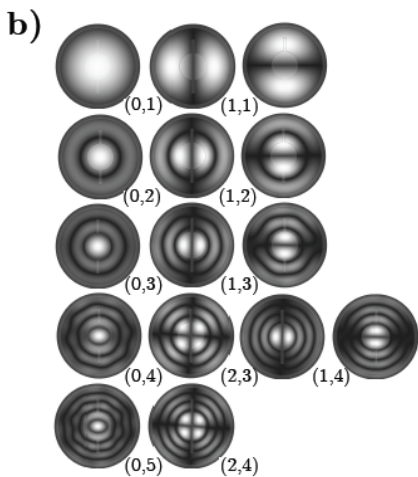
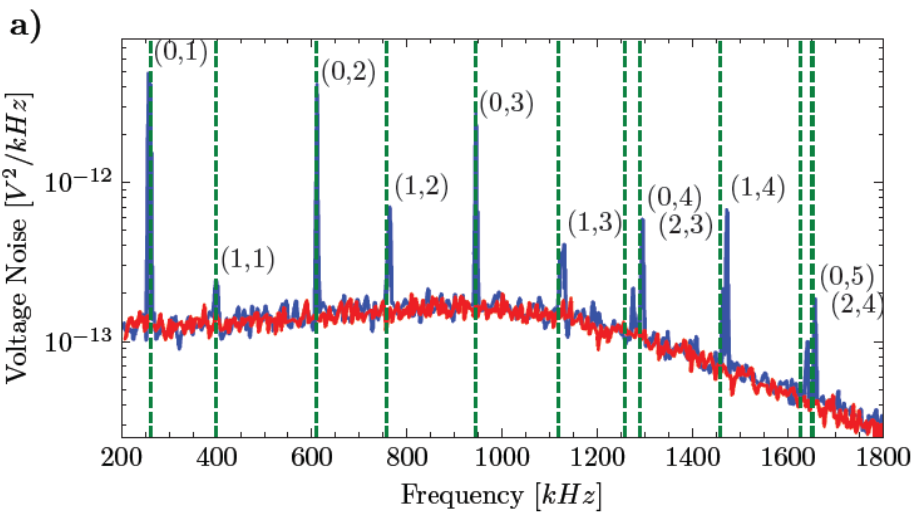
Right: The device clamped to the OFHC copper block, and the diving PCB board used in the optical setup

Optical image of the SiN stoichiometric nanomembrane (light blue) with the TiN layer (brown). The membrane is endowed with the on-chip shield for recoil losses (right). Detailed view of the TiN notch in the membrane electrode used for the mode identification and the component assembly

# Mechanical modes characterization via optical homodyne detection



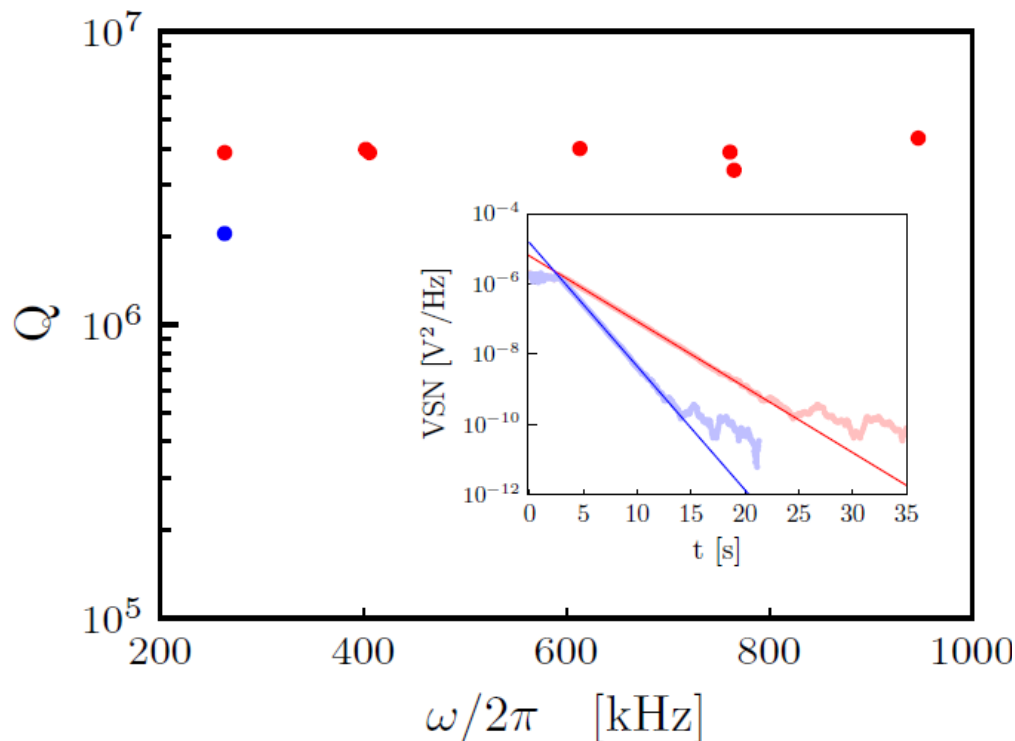
Michelson interferometer with shot noise limited homodyne detection



**a) Voltage spectral noise of the homodyne signal (blue) and the shot-noise contribution (red). The green dashed lines are the calculated frequencies from the FEM simulation.**  
**b) Calculated mode shapes by FEM simulation, corresponding to the calculated mode frequencies present in the spectrum.**



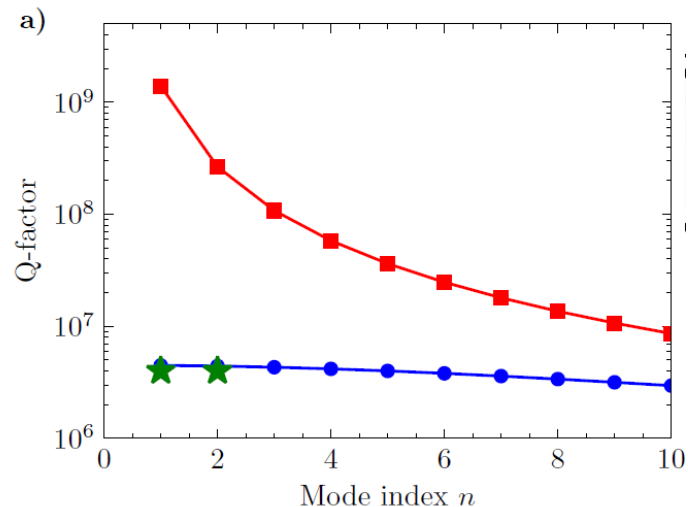
# MEASUREMENT OF THE QUALITY FACTOR: TARGET VALUE ACHIEVED



Measurement of the mechanical Q-factor for different modes after the final assembling of the device. Red points correspond to measurements at  $V_{DC}=0V$ , the blue point corresponds to the measurement at  $V_{DC}=30V$ .

Inset: voltage spectral noise (VSN) density of the homodyne signal during the ring-down measurement of the fundamental mode (0,1)

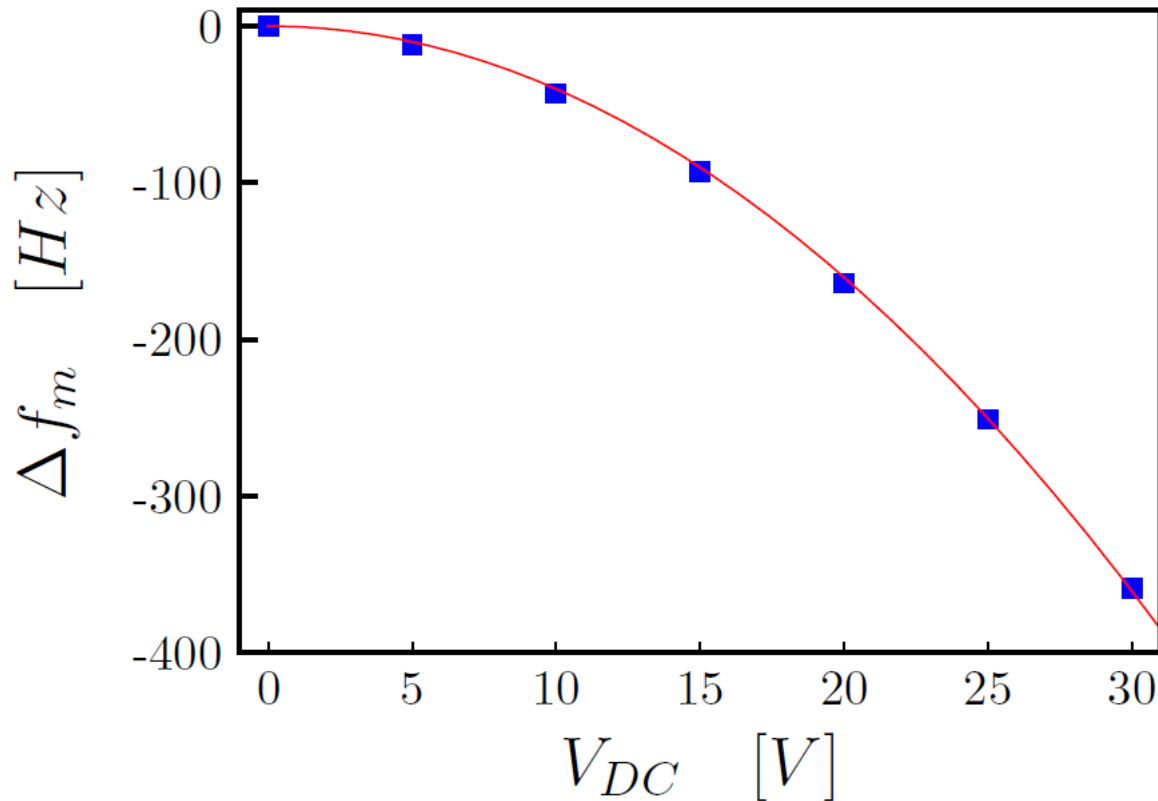
**Agreement with theory (blue dots and green stars)**  
Red dots: Q without edge losses of the SiN layer (theory)



Losses are dominated by edge losses of the SiN layer  
 $\Rightarrow$  Thickness and shape of the metal coating on a stressed membrane can be arbitrary if **patterning starts from a few microns of the membrane's edge.**



# Electro-mechanical characterization of the device



Measurement of the frequency shift of the (1,1) mode as a function of the DC voltage bias. The red line is the fit of the data,  $\Rightarrow$

average distance between the electrodes and the membrane  $d = 5.12 \mu\text{m}$ , (using the parameters: effective area  $A_{\text{eff}} = 0.075 \text{ mm}^2$ ; membrane mass  $m_{\text{eff}} = 420 \text{ ng}$ ; unperturbed mode frequency  $f_0 = f_{11} = 399587 \text{ Hz}$ ).

$$\Delta f_m = -\frac{\epsilon_0}{8\pi^2} \frac{A_{\text{eff}}}{m_{\text{eff}} d^3 f_0} V_{DC}^2$$

# FUTURE ACTIVITIES AND PERSPECTIVES

Research keeps on going via

PRIN 2022 **“Quantum transduction and sensing with opto-electro-mechanical systems”** (PI: Unicam + INFN TIPFA + CNR-IMEM Trento)

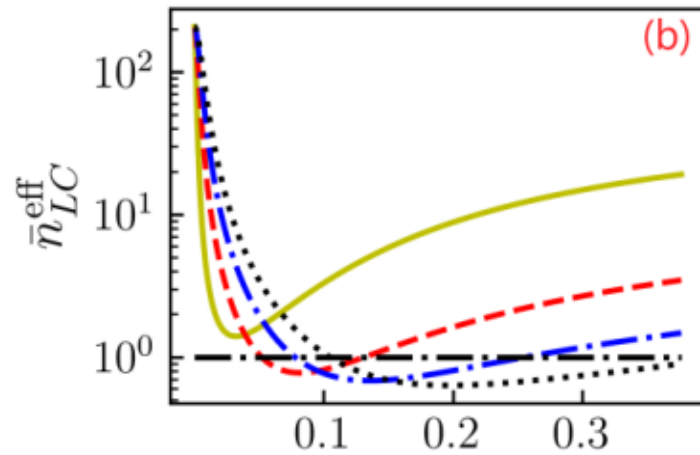
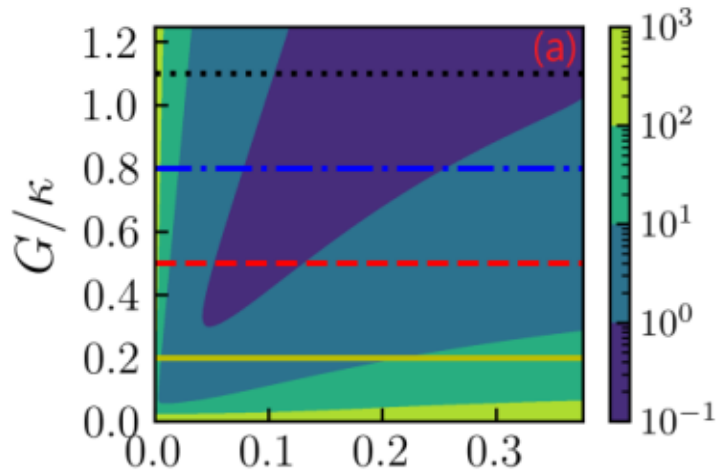
## TECHNICAL IMPROVEMENTS

- Improving devices yield and reproducibility;
- Avoid electrical cross-talk between the membrane capacitor and the electrode (oxide passivation) for a large span of voltage biases
- Better control of the capacitor plate distance

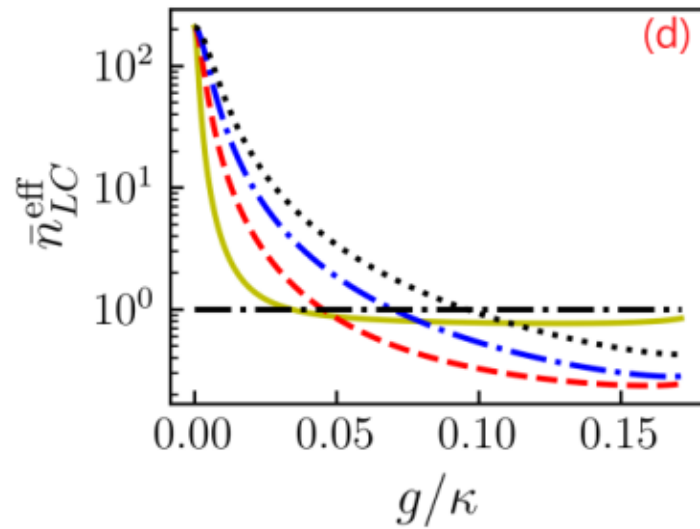
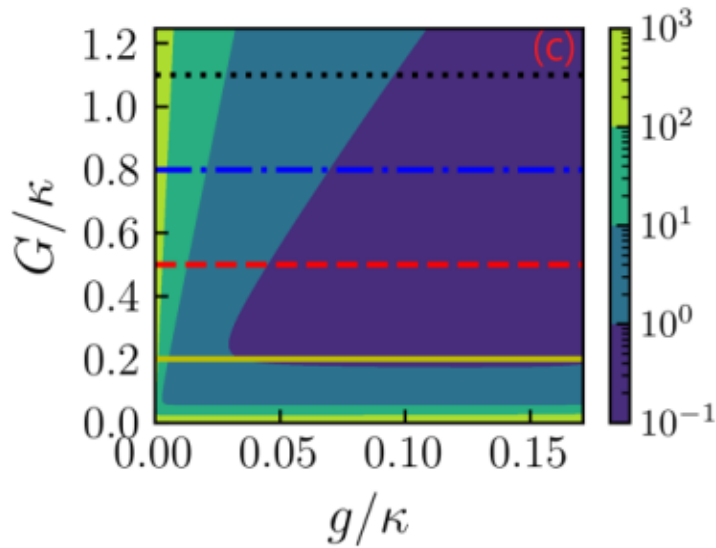
## PHYSICS AND DEVICES

1. **“Sympathetic” cooling to the quantum ground state of an LC resonator**: laser cooling of the SiN membrane which then sympathetically cools the coupled quasi-resonant LC rf-circuit
2. **Nonreciprocal rf-optical transduction** via interference

# Ground state sympathetic cooling of the LC is possible



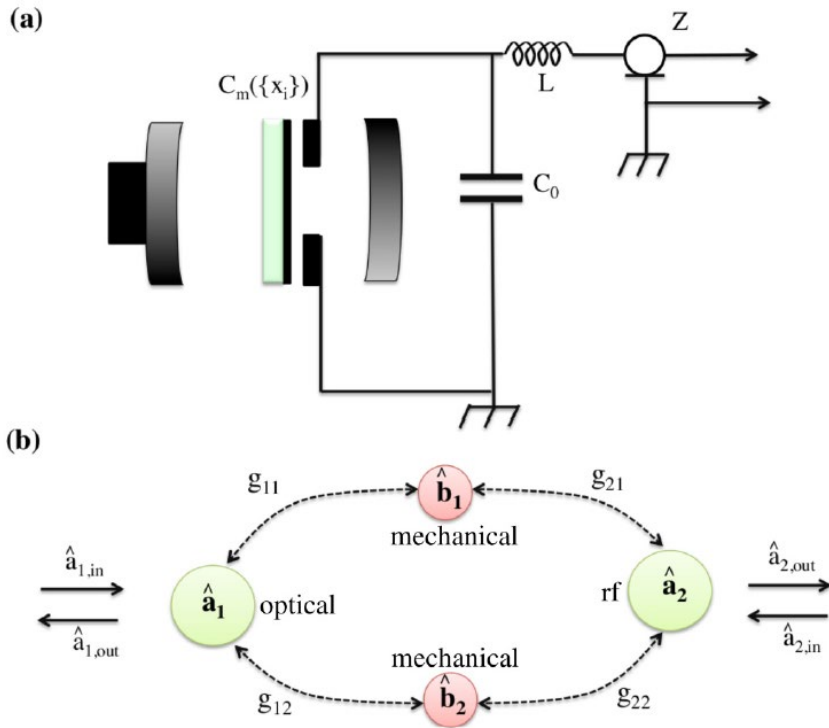
Exact results for the stationary LC circuit occupancy  $n_{\text{eff}}^{\text{LC}}$



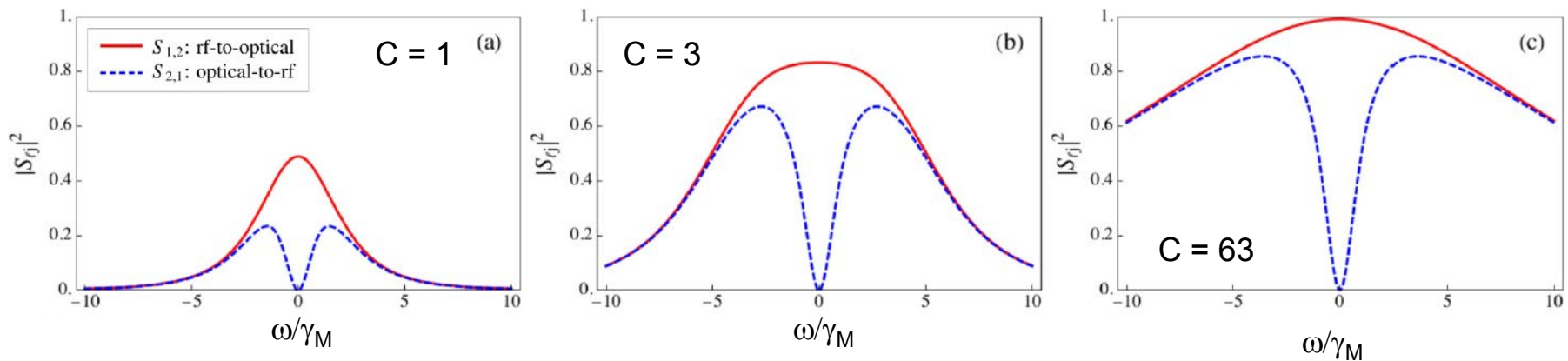
LC-mechanical are always kept on resonance by adjusting parameters

$$Q_{LC} = 4 \times 10^4 \quad T = 10 \text{ mK}$$

# Nonreciprocal conversion between radio-frequency and optical photons with an optoelectromechanical system



N. Eshaqi-Sani et al, Phys. Rev. A 106, 032606 (2022)



Equal electromechanical and optomechanical cooperativities  $C$